

Radiation Tolerance and Charge Trapping Enhancement of ALD HfO₂/Al₂O₃ Nanolaminated Dielectrics

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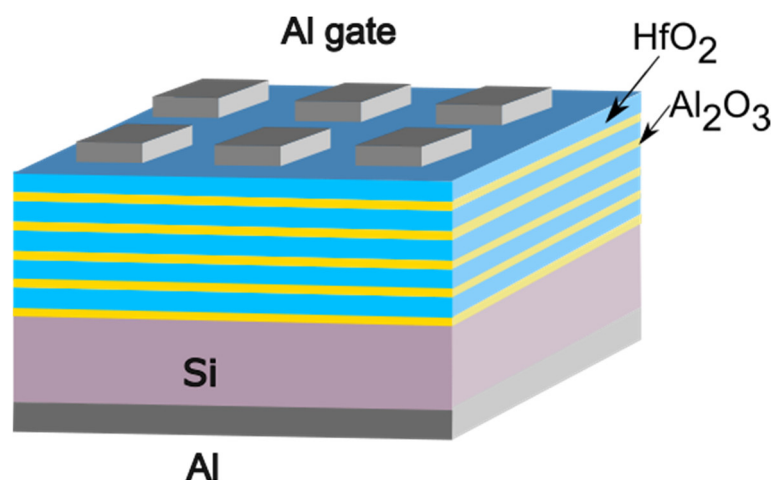


Figure S1. A schematic presentation of a test wafer with MIS capacitors, blue layers—HfO₂, yellow Al₂O₃.

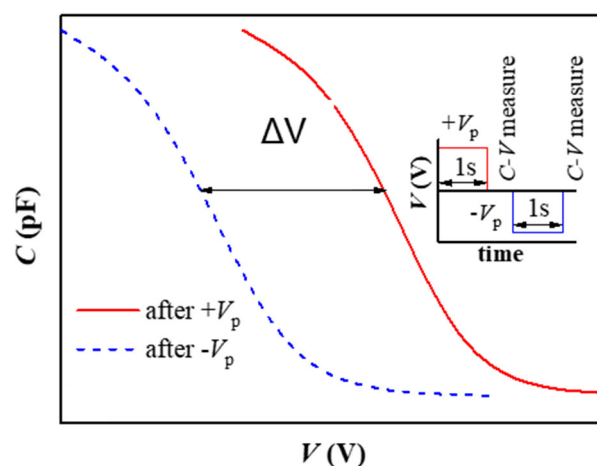


Figure S2. An illustration of the memory window definition. The memory window, ΔV is defined as the difference in the position of the measured C-V curves at flat band capacitance C_{fb} after applying consecutively positive voltage pulse ($+V_p$) and negative voltage pulse ($-V_p$). The inset shows the measurement procedure.

Citation: Spassov, D.; Paskaleva, A.; Guzewicz E.; Davidović V.; Srbojub S.; Djorić-Veljković, S.; Ivanov T.; Stanchev, T.; Stojadinović N. Radiation Tolerance and Charge Trapping Enhancement of ALD HfO₂/Al₂O₃ Nanolaminated Dielectrics. *Materials* **2021**, *14*, 849. <https://doi.org/10.3390/ma14040849>

Academic Editors: Alain Moissette and Antonio Di Bartolomeo
Received: 6 January 2021
Accepted: 8 February 2021
Published: 10 February 2021

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